



SANYO Semiconductors

## DATA SHEET

# 2SK4062LS — N-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- Low ON-resistance, low input capacitance, ultrahigh-speed switching.
- High reliability (Adoption of HVP process).
- Attachment workability is good by Mica-less package.
- Avalanche resistance guarantee.

### Specifications

Absolute Maximum Ratings at  $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	$V_{DSS}$		450	V
Gate-to-Source Voltage	$V_{GSS}$		$\pm 30$	V
Drain Current (DC)	$I_{DC}^{*1}$	Limited only by maximum temperature	18	A
	$I_{Dpack}^{*2}$	SANYO's ideal heat dissipation condition	13.6	A
Drain Current (Pulse)	$I_{DP}$		72	A
Allowable Power Dissipation	PD		2.0	W
		$T_c=25^\circ\text{C}$ (SANYO's ideal heat dissipation condition)	45	W
Channel Temperature	$T_{ch}$		150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$		-55 to +150	$^\circ\text{C}$
Avalanche Energy (Single Pulse) *3	$E_{AS}$		1.03	J
Avalanche Current *4	$I_{AV}$		18	A

\*1 Shows chip capability

\*2 Package limited

\*3  $V_{DD}=99\text{V}$ ,  $L=5\text{mH}$ ,  $I_{AV}=18\text{A}$

\*4  $L \leq 5\text{mH}$ , single pulse

Marking : K4062

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**SANYO Semiconductor Co., Ltd.**

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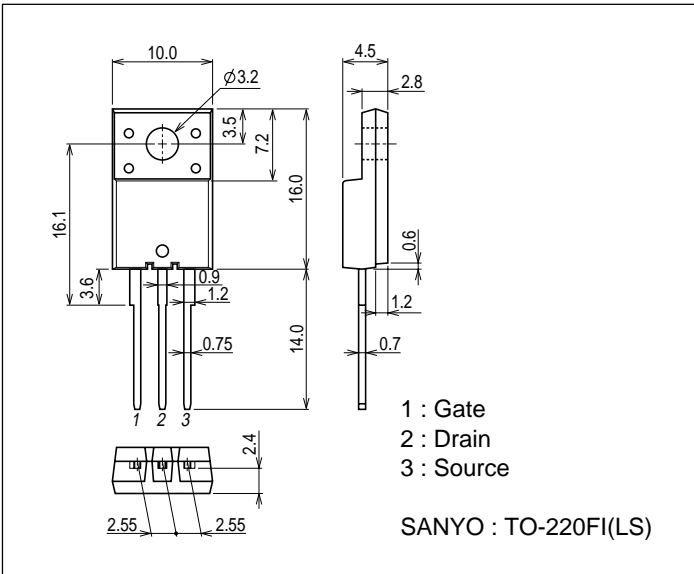
# 2SK4062LS

## Electrical Characteristics at Ta=25°C

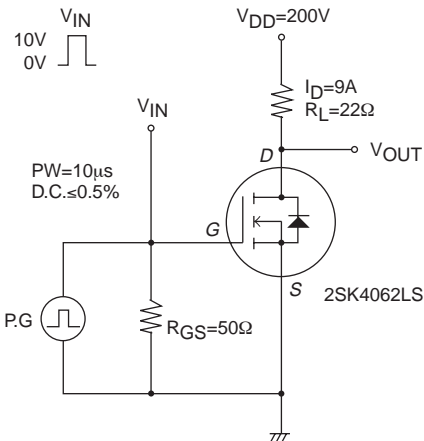
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0V$	450			V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=450V, V_{GS}=0V$			100	$\mu A$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 30V, V_{DS}=0V$			$\pm 100$	nA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	3		5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=9A$	6	12		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	$I_D=9A, V_{GS}=15V$		0.24	0.32	$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS}=30V, f=1MHz$		2150		pF
Output Capacitance	$C_{oss}$	$V_{DS}=30V, f=1MHz$		230		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS}=30V, f=1MHz$		15		pF
		$V_{DS}=5V, f=1MHz$		31		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		52		ns
Rise Time	$t_r$	See specified Test Circuit.		114		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		78		ns
Fall Time	$t_f$	See specified Test Circuit.		70		ns
Total Gate Charge	$Q_g$	$V_{DS}=200V, V_{GS}=10V, I_D=18A$		39		nC
Gate-to-Source Charge	$Q_{gs}$	$V_{DS}=200V, V_{GS}=10V, I_D=18A$		15		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$	$V_{DS}=200V, V_{GS}=10V, I_D=18A$		15		nC
Diode Forward Voltage	$V_{SD}$	$I_S=18A, V_{GS}=0V$		0.97	1.2	V

## Package Dimensions

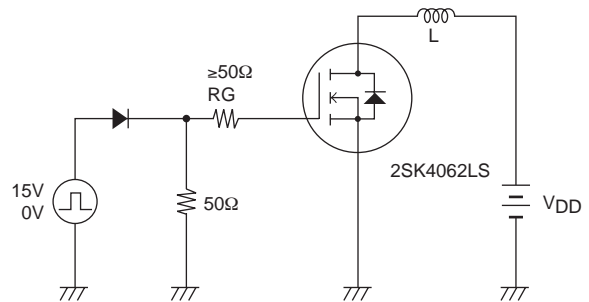
unit : mm (typ)  
7509-002



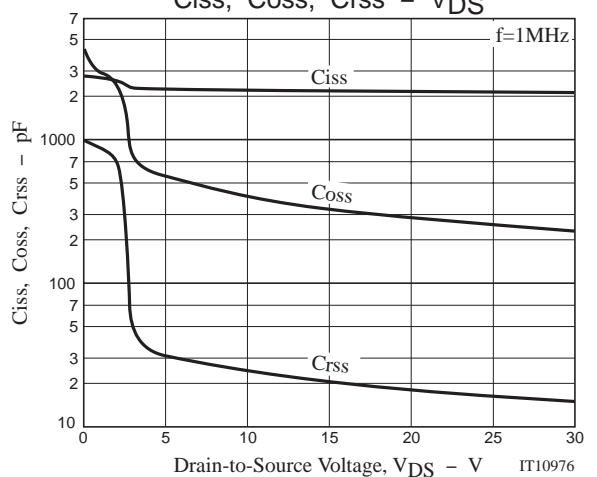
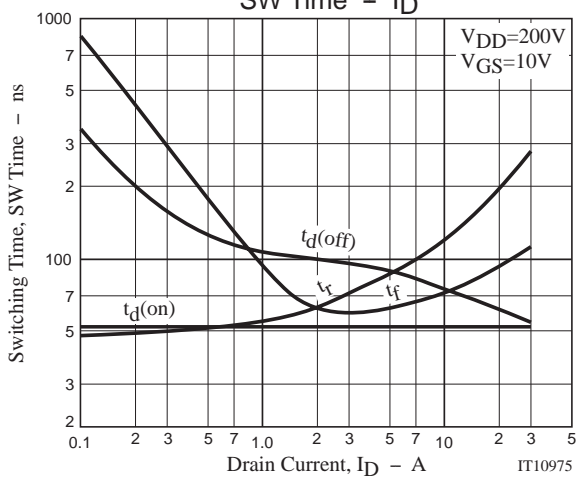
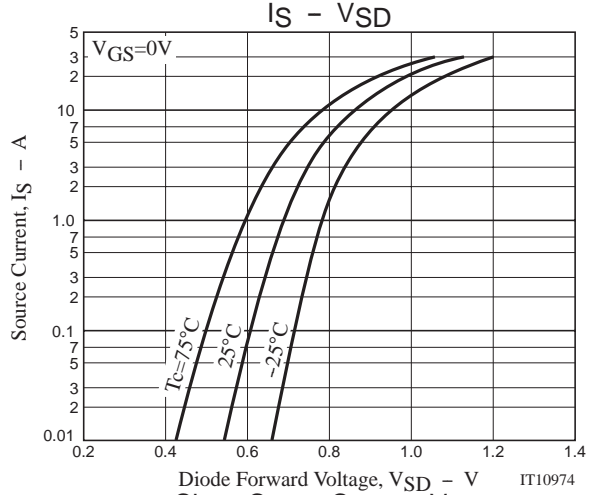
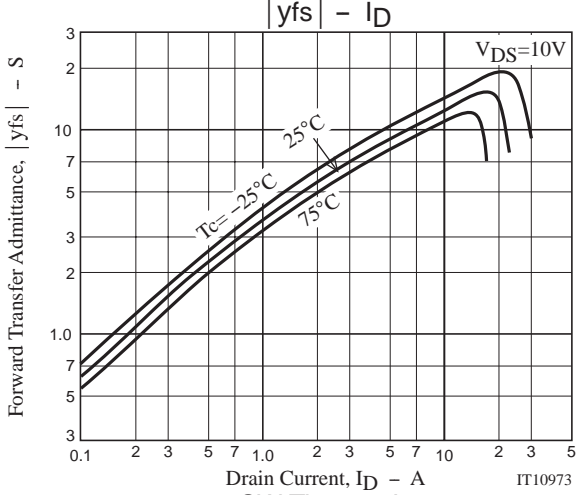
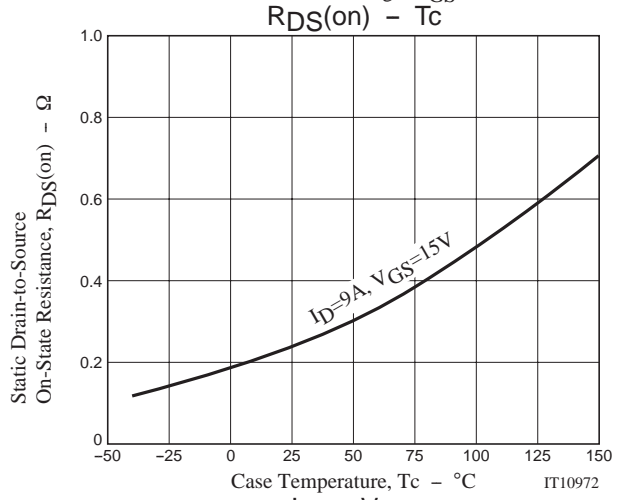
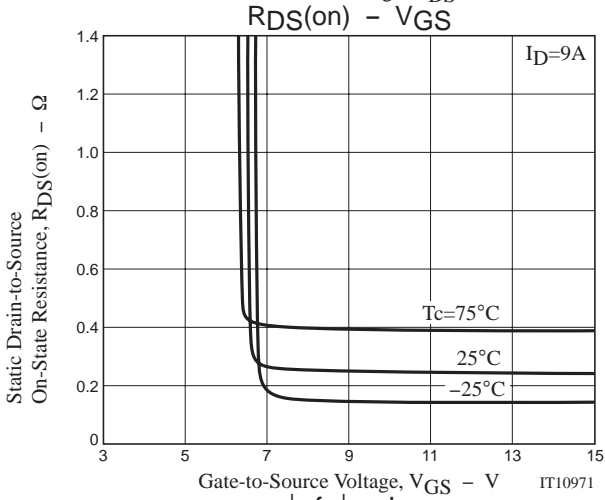
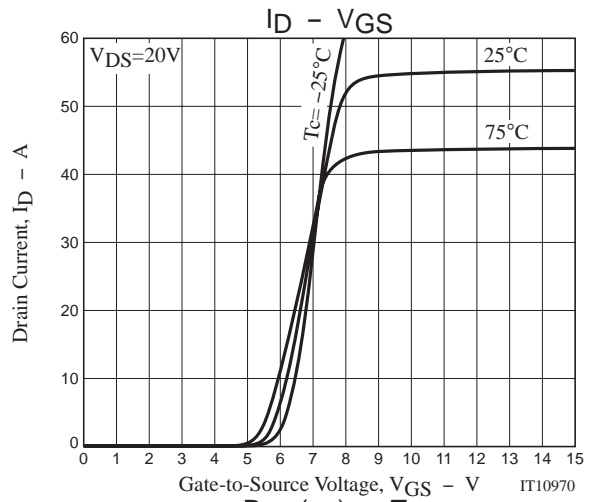
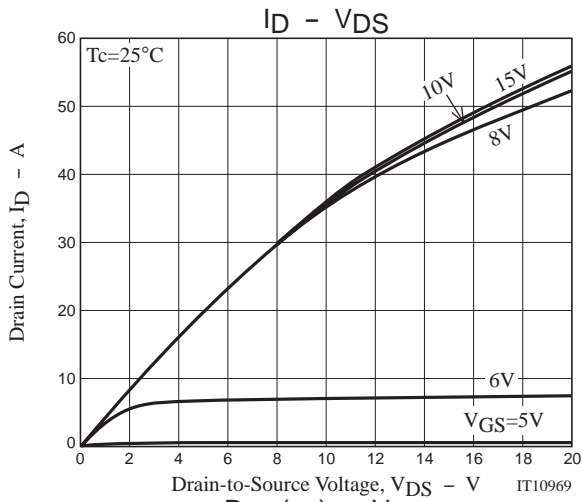
## Switching Time Test Circuit



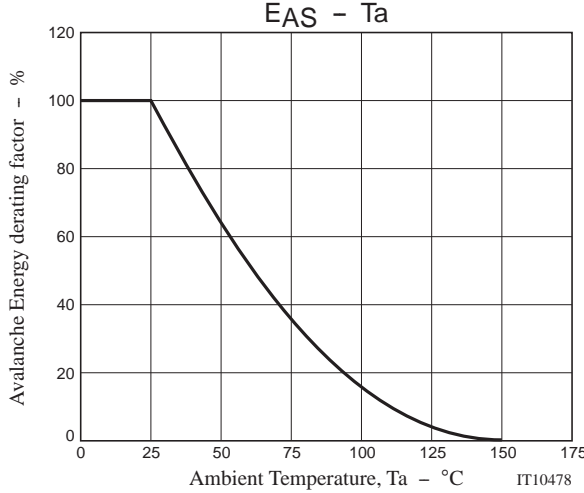
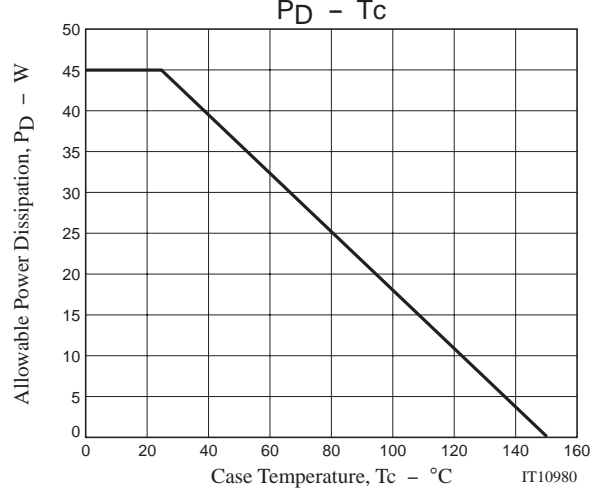
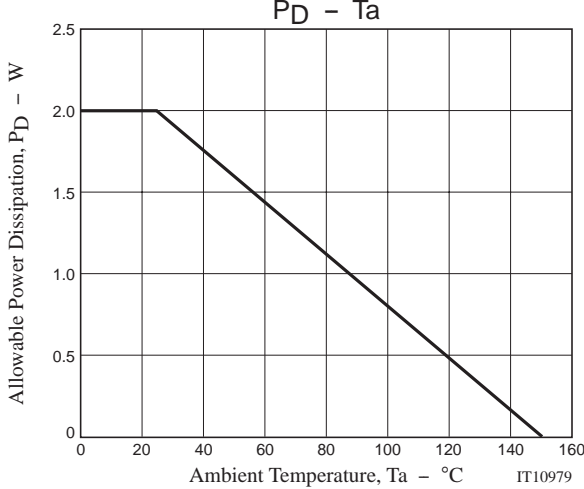
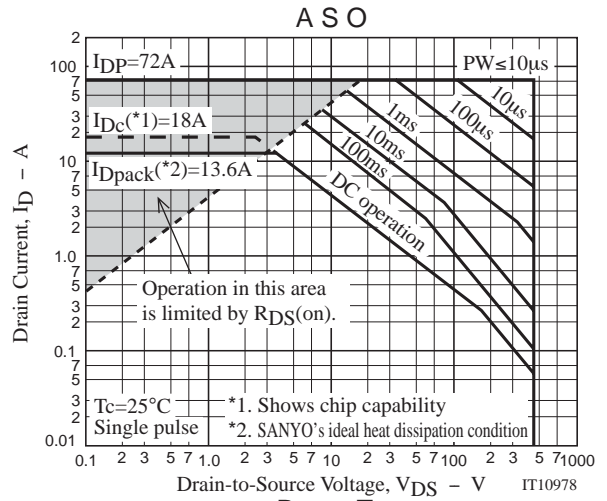
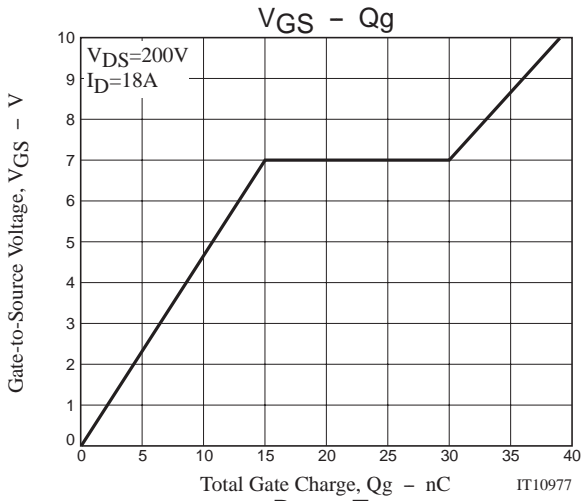
## Avalanche Resistance Test Circuit



# 2SK4062LS



# 2SK4062LS



Note on usage : Since the 2SK4062LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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